



#### 200V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
-200V	25Ω @ V <sub>GS</sub> = 10V	200mA	

## **Description**

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

## **Applications**

Active clamping of primary aide MOSFETs in 48 Volt DC-DC converters

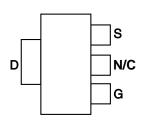
### **Features and Benefits**

- High Voltage
- Low On-resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

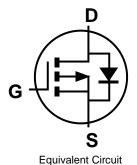
#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3)
- Weight: 0.112 grams (Approximate)





Pin Out - Top



Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP2120G4TA	ZXMP2120	7	12	1,000
ZXMP2120G4TC	ZXMP2120	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

SOT223

ZXMP2120 = Product Type Marking Code YWW = Date Code Marking Y or Y = Last Digit of Year (ex: 5 = 2015) WW or WW = Week Code (01~53)



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-200	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (V <sub>GS</sub> = 10V; T <sub>A</sub> = +25°C) (Note 5)	I <sub>D</sub>	-200	mA
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-1	A
Pulsed Source Current (Body Diode) (Note 6)	I <sub>SM</sub>	-1	A

# Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T <sub>A</sub> = +25°C (Note 5)	D-	2.0	W
Linear Derating Factor	P <sub>D</sub>	1.6	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	62.5	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

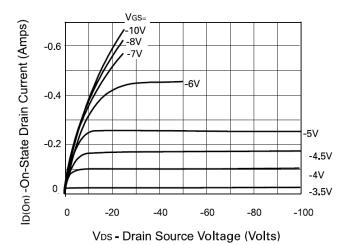
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-200	-	-	V	$V_{GS} = 0V$ , $I_D = -1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	-10 -100	μA	$V_{DS} = -200V, V_{GS} = 0V$ $V_{DS} = -160V, V_{GS} = 0V, T = +125$ °C	
Gate-Source Leakage	I <sub>GSS</sub>	-	-	20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.5	-	-3.5	V	$V_{DS} = V_{GS}$ , $I_D = -1mA$	
Static Drain-Source On-Resistance (Note 7)	R <sub>DS(ON)</sub>	-	-	25	Ω	$V_{GS} = -10V, I_D = -150mA$	
Forward Transconductance (Notes 7 & 8)	<b>g</b> fs	50	-	-	mS	$V_{DS} = -25V, I_{D} = -150mA$	
On-State Drain Current (Note 7)	I <sub>D(ON)</sub>	-300	-	-	mA	$V_{DS} = -25V, V_{GS} = -10V$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 8)	C <sub>iss</sub>	-	-	100	pF	V 05V V 0V	
Output Capacitance (Note 8)	Coss	-	-	25	pF	$V_{DS} = -25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance (Note 8)	C <sub>rss</sub>	-	-	7	pF		
Turn-On Delay Time (Notes 8 & 9)	t <sub>D(ON)</sub>	-	-	7	ns		
Turn-On Rise Time (Notes 8 & 9)	t <sub>R</sub>	-	-	15	ns	V 25V I 450m A	
Turn-Off Delay Time (Notes 8 & 9)	t <sub>D(OFF)</sub>	-	-	12	ns	$V_{DD} = -25V, I_D = -150mA$	
Turn-Off Fall Time (Notes 8 & 9)	t <sub>F</sub>	-	-	15	ns		

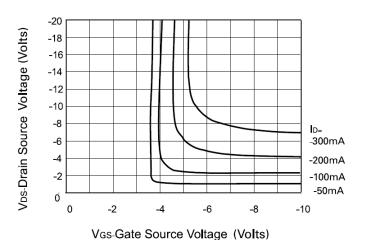
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. Repetitive rating pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.
- 7. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.
- 9. Switching characteristics are independent of operating junction temperature.

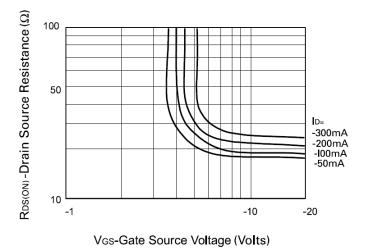




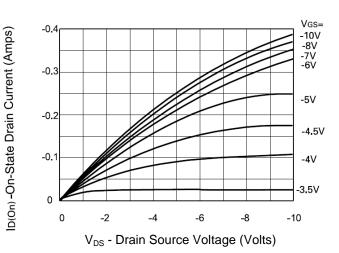
### **Output Characteristics**



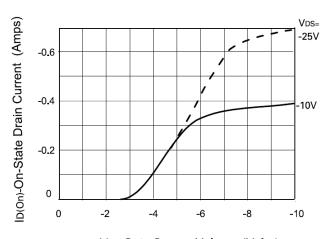
## **Voltage Saturation Characteristics**



On-resistance vs gate-source voltage

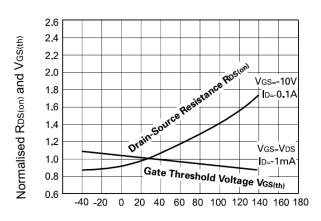


#### **Saturation Characteristics**



VGS-Gate Source Voltage (Volts)

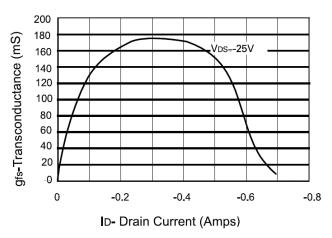
Transfer Characteristics



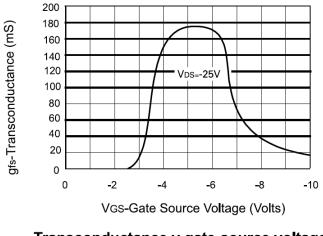
T-Temperature (°C)

Normalised RDs(on) and Vgs(th) vs Temperature

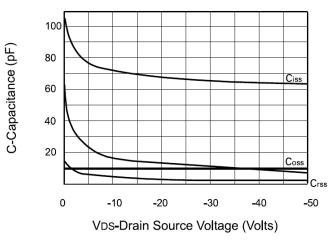




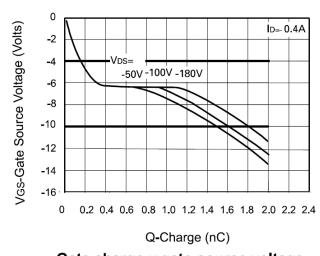
## Transconductance v drain current



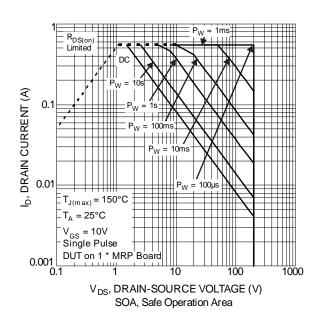
#### Transconductance v gate-source voltage



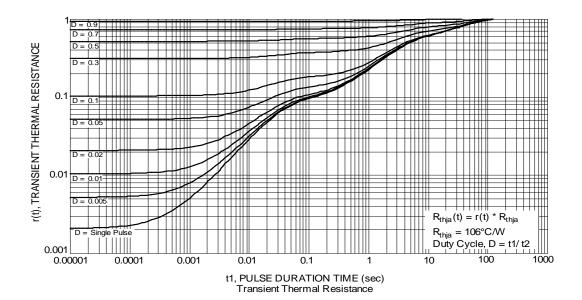
Capacitance v drain-source voltage



Gate charge v gate-source voltage



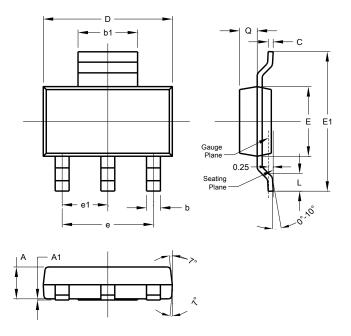






## **Package Outline Dimensions**

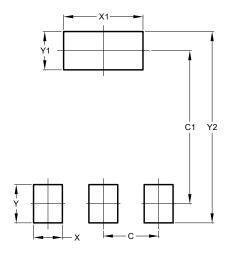
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
Q	0.84	0.94	0.89	
All Dimensions in mm				

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)	
С	2.30	
C1	6.40	
Х	1.20	
X1	3.30	
Y	1.60	
Y1	1.60	
Y2	8.00	

May 2015



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